

L Number	Hits	Search Text	DB	Time stamp
15	4	(US-5423944-\$ or US-6326218-\$ or US-6451665-\$).did. or (EP-782177-\$).did.	USPAT; EPO	2003/06/18 15:11
34	5	(US-6326218-\$ or US-6432835-\$ or US-6451665-\$ or US-6506636-\$ or US-6512182-\$).did.	USPAT	2003/06/18 15:11
35	7	((US-6326218-\$ or US-6432835-\$ or US-6451665-\$ or US-6506636-\$ or US-6512182-\$).did.) or ((US-5423944-\$ or US-6326218-\$ or US-6451665-\$).did. or (EP-782177-\$).did.)	USPAT; EPO; JPO	2003/06/18 15:12
36	3	((US-6326218-\$ or US-6432835-\$ or US-6451665-\$ or US-6506636-\$ or US-6512182-\$).did.) or ((US-5423944-\$ or US-6326218-\$ or US-6451665-\$).did. or (EP-782177-\$).did.)) and wet adj3 (etch\$3)	USPAT; EPO; JPO	2003/06/18 15:14
37	353394	platinum pt ruthenium ru rhodium rh palladium pd iridium ir	USPAT; EPO; JPO	2003/06/18 15:13
38	5006	(platinum pt ruthenium ru rhodium rh palladium pd iridium ir ) and wet adj3 (etch\$3)	USPAT; EPO; JPO	2003/06/18 15:14
39	918	((platinum pt ruthenium ru rhodium rh palladium pd iridium ir ) and wet adj3 (etch\$3)) and (NaCl "sodium chloride" KCl "potassium chloride" CaCl "calcium chloride" HCl "hydrochloric acid" "liquid salt")	USPAT; EPO; JPO	2003/06/18 15:17
40	320985	NaCl "sodium chloride" KCl "potassium chloride" CaCl "calcium chloride" HCl "hydrochloric acid" "liquid salt"	USPAT; EPO; JPO	2003/06/18 15:18
41	31912	(NaCl "sodium chloride" KCl "potassium chloride" CaCl "calcium chloride" HCl "hydrochloric acid" "liquid salt") same (platinum pt ruthenium ru rhodium rh palladium pd iridium ir )	USPAT; EPO; JPO	2003/06/18 15:18
42	4783	(NaCl "sodium chloride" KCl "potassium chloride" CaCl "calcium chloride" HCl "hydrochloric acid" "liquid salt") adj10 (platinum pt ruthenium ru rhodium rh palladium pd iridium ir )	USPAT; EPO; JPO	2003/06/18 15:21
43	4	(NaCl "sodium chloride" KCl "potassium chloride" CaCl "calcium chloride" HCl "hydrochloric acid" "liquid salt") adj10 (platinum pt ruthenium ru rhodium rh palladium pd iridium ir ) adj15 (wet adj3 etch\$3)	USPAT; EPO; JPO	2003/06/18 15:22
44	65	(wet adj3 etch\$3) adj5 (platinum pt ruthenium ru rhodium rh palladium pd iridium ir )	USPAT; EPO; JPO	2003/06/18 16:17
45	1	5515984.pn.	USPAT; EPO; JPO	2003/06/18 15:30
46	0	(wet adj3 etch\$3) adj5 "noble metals"	USPAT; EPO; JPO	2003/06/18 16:18
47	56	(etch\$3) adj5 "noble metals"	USPAT; EPO; JPO	2003/06/18 16:18
-	294959	capacitor	USPAT; EPO; JPO	2003/06/17 18:25
-	353394	platinum pt ruthenium ru rhodium rh palladium pd iridium ir	USPAT; EPO; JPO	2003/06/18 15:13
-	12300	(O3 ozone) and (water steam H2O) and (halgenide Fluoride Chloride Bromide iodide)	USPAT; EPO; JPO	2003/06/17 18:28
-	448	(O3 ozone) and (water steam H2O) and (halgenide Fluoride Chloride Bromide iodide) same (etch etching etcher etchant)	USPAT; EPO; JPO	2003/06/17 18:39
-	20324	capacitor and (platinum pt ruthenium ru rhodium rh palladium pd iridium ir)	USPAT; EPO; JPO	2003/06/17 18:29

-	44	(capacitor and (platinum pt ruthenium ru rhodium rh palladium pd iridium ir)) and ((O3 ozone) and (water steam H2O) and (halgenide Fluoride Chloride Bromide iodide) same (etch etching etcher etchant))	USPAT; EPO; JPO	2003/06/18 15:12
-	27	(O3 ozone) same (water steam H2O) same (halgenide Fluoride Chloride Bromide iodide halogen F2 Cl2 Br2 I2) same (etch etching etcher etchant)	USPAT; EPO; JPO	2003/06/17 18:48
-	6	8-153707	USPAT	2003/06/18 12:18
-	0	8-153707	JPO	2003/06/18 12:20
-	0	08-153707	JPO	2003/06/18 12:20
-	0	"08-153707"	JPO	2003/06/18 12:20
-	0	"manufacturing method for semiconductor device".ti.	JPO	2003/06/18 12:21
-	0	"manufacturing method for semiconductor device"	JPO	2003/06/18 12:21
-	178515	takeshi.inv.	JPO	2003/06/18 12:21
-	121	takeshi.inv. and Ruthenium	JPO	2003/06/18 12:21
-	1	(takeshi.inv. and Ruthenium) and SOG	JPO	2003/06/18 12:22